TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

T A 4 O O 3 F

VHF~UHF WIDE BAND AMPLIFIER

FEATURES

Band Width 1.5CHz (Typ.) (3dB down, $V_{CC} = 2V$)

High Gain: $|S_{21}|^2 = 11$ dB (Typ.), (f = 500MHz, $V_{CC} = 2V$)

Operating Supply Voltage: V_{CC} = 2~3V

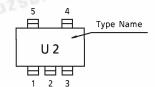
Low Current Operation : $I_{CC} = 3.5 \text{mA}$ (Typ.) ($V_{CC} = 2V$)

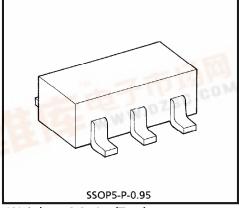
Small Package

Marking



PIN ASSIGNMENT (TOP VIEW)





Weight: 0.014g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|-------------------------|------------------|----------------|------|
| Supply Voltage | Vcc | 4 | V |
| Total Power Dissipation | P _D * | 300 | mW |
| Operating Temperature | T _{opr} | - 40∼85 | °C |
| Storage Temperature | T _{stg} | - 55~125 | °C |

When mounted glass epoxy of 2.5cm² x 1.6t

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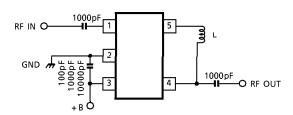
TOSHIBA TA4003F

ELECTRICAL CHARACTERISTICS (Ta = 25°C) (Note 1)

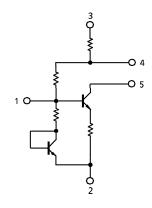
| CHARACTERISTIC | SYMBOL | TEST CIR- CUIT | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|----------------------|--------------------------------|----------------------|--|------|-------|------|------|
| Circuit Current | lcc | _ | V _{CC} = 2V, Non carrier | 2.5 | 3.5 | 4.5 | mA |
| Insertion Gain | S ₂₁ ² | 1 | V _{CC} = 2V, f = 500MHz | 9 | 11 | 14 | dB |
| Band Width | BW | 1 | V _{CC} = 2V (Note 2) | 1.2 | 1.5 | _ | GHz |
| Noise Figure | NF | 1 | V _{CC} = 2V, f = 500MHz | _ | 5.2 | 7 | dB |
| Input Return Loss | $ S_{11} ^2$ | 1 | $V_{CC} = 2V$, $f = 500MHz$ | _ | - 7.5 | _ | dB |
| Output Return Loss | $ S_{22} ^2$ | 1 | $V_{CC} = 2V$, $f = 500MHz$ | _ | - 7.5 | _ | dB |
| Isolation | S ₁₂ ² | 1 | V _{CC} = 2V, f = 500MHz | _ | - 24 | _ | dB |
| Maximum Output Level | Po | 1 | V _{CC} = 2V, f = 500MHz, Pin = 0dBmW | _ | 0 | _ | dBmW |

Note 1 : Have use for connect inductance between terminal 4 and 5 Note 2 : BW is frequency of 3dB down from $|S_{21}|^2$ at 500MHz. 8nH at $V_{CC} = 2V$

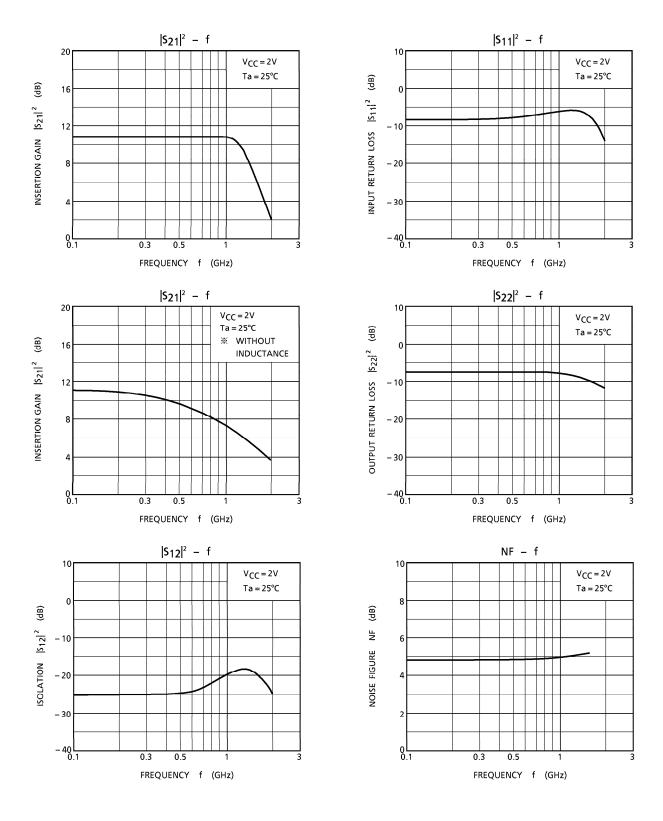
TEST CIRCUIT 1. (TOP VIEW)



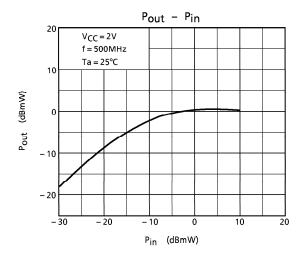
EQUIVALENT CIRCUIT

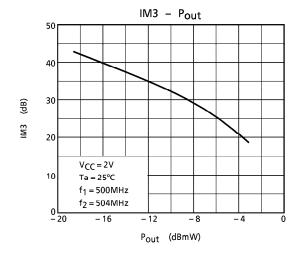


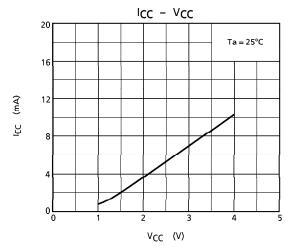
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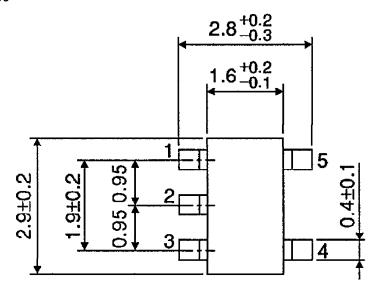


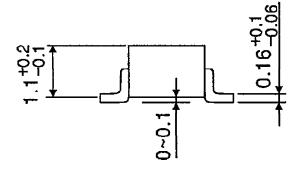


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OUTLINE DRAWING SSOP5-P-0.95

Unit: mm





Weight: 0.014g (Typ.)